MAX6198xESA Rev. A

RELIABILITY REPORT

FOR

MAX6198xESA

PLASTIC ENCAPSULATED DEVICES

November 27, 2001

MAXIM INTEGRATED PRODUCTS

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SUNNYVALE, CA 94086

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Conclusion

The MAX6198 successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX6198x precision, micro-power, low-dropout voltage reference offers high initial accuracy and very low temperature coefficient through proprietary curvature-correction circuit and laser-trimmed precision thin-film resistors.

This series-mode bandgap reference draws a maximum of only 35μ A quiescent supply current, making it ideal for battery-powered instruments. It offers a supply current that is virtually immune to input voltage variations. Load-regulation specifications are guaranteed for source and sink currents up to 500μ A. The MAX6195 is internally compensated, making it ideal for applications that require fast settling, and are stable with capacitive loads up to 2.2nF.

B. Absolute Maximum Ratings

ltem	Rating
Voltages Referenced to GND	
IN	-0.3V to +13.5V
OUT	-0.3V to (V _{IN} + 0.3V)
Output Short Circuit to GND or IN ($V_{IN} < 6V$)	Continuous
Output Short Circuit to GND or IN (VIN 6V)	60sec
Storage Temperature Range	-65°C to +150°C
Lead Temp. (10 sec.)	+300°C
Power Dissipation	
8-Pin NSO	471mW
Derates above +70°C	
8-Pin NSO	5.88mW/°C

II. Manufacturing Information

A. Description/Function:	Precision, Micropower, Low-Dropout Voltage Reference
B. Process:	S12 (SG1.2) - Standard 1.2 micron silicon gate CMOS
C. Number of Device Transistors:	70
D. Fabrication Location:	Cailfornia or Oregon, USA
E. Assembly Location:	Malaysia or Korea
F. Date of Initial Production:	November, 1998

III. Packaging Information

A. Package Type:	8 Lead Small Outline
B. Lead Frame:	Copper
C. Lead Finish:	Solder Plate
D. Die Attach:	Silver-filled Epoxy
E. Bondwire:	Gold (1.3 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	Buildsheet # 05-0901-0152
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard JESD22-A112:	Level 1

IV. Die Information

A. Dimensions:	44 x 31 mils
B. Passivation:	Si_3N_4/SiO_2 (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Aluminum/Copper/Si
D. Backside Metallization:	None
E. Minimum Metal Width:	1.2 microns (as drawn)
F. Minimum Metal Spacing:	1.2 microns (as drawn)
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

Α.	Quality Assurance Contacts:	Jim Pedicord	(Reliability Lab Manager)
		Bryan Preeshl	(Executive Director of QA)
		Kenneth Huening	(Vice President)
В.	Outgoing Inspection Level:	0.1% for all electri 0.1% For all Visu	cal parameters guaranteed by the Datasheet. al Defects.

- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate (λ) is calculated as follows:

 $\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4389 \times 160 \times 2}$ (Chi square value for MTTF upper limit) Temperature Acceleration factor assuming an activation energy of 0.8eV $\lambda = 6.79 \times 10^{-9}$ $\lambda = 6.79 \text{ F.I.T.}$ (60% confidence level @ 25°C)

This low failure rate represents data collected from Maxim's reliability qualification and monitor programs. Maxim also performs weekly Burn-In on samples from production to assure reliability of its processes. The reliability required for lots which receive a burn-in qualification is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on rejects from lots exceeding this level. The attached Burn-In Schematic (Spec. # 06-5387) shows the static circuit used for this test. Maxim also performs 1000 hour life test monitors quarterly for each process. This data is published in the Product Reliability Report (**RR-1L**).

B. Moisture Resistance Tests

Maxim evaluates pressure pot stress from every assembly process during qualification of each new design. Pressure Pot testing must pass a 20% LTPD for acceptance. Additionally, industry standard 85°C/85%RH or HAST tests are performed quarterly per device/package family.

C. E.S.D. and Latch-Up Testing

The RF23-2 die type has been found to have all pins able to withstand a transient pulse of ± 2500 V, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of ± 250 mA and/or ± 20 V.

Table 1Reliability Evaluation Test Results

MAX6198xESA

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Tes	t (Note 1)			
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	160	0
Moisture Testi	ng (Note 2)			
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality	1819	15
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	77	0
Mechanical St	ress (Note 2)			
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters (generic test vehicle)	77	0

Note 1: Life Test Data may represent plastic D.I.P. qualification lots for the Small Outline package. Note 2: Generic Package/Process data

Attachment #1

	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)
1.	All pins except V _{PS1} 3/	All V _{PS1} pins
2.	All input and output pins	All other input-output pins

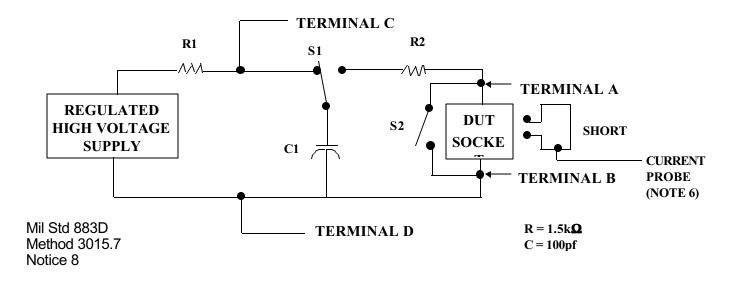
TABLE II. Pin combination to be tested. 1/2/

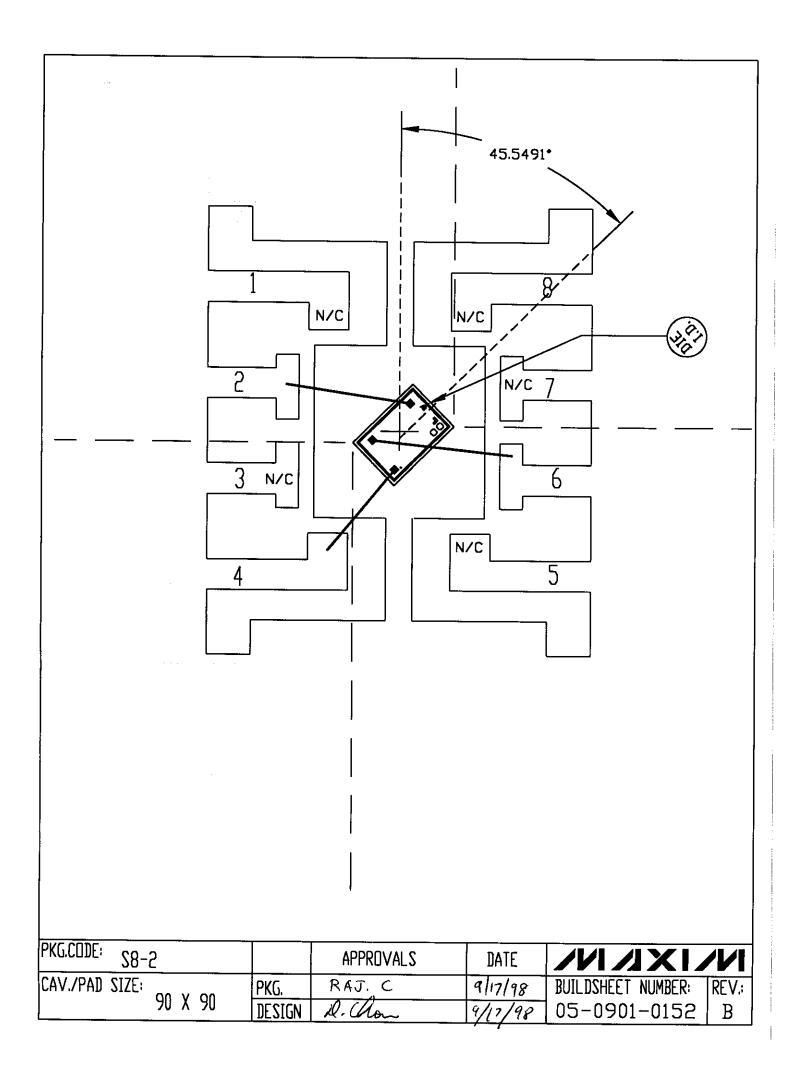
- 1/ Table II is restated in narrative form in 3.4 below.
- $\overline{2/}$ No connects are not to be tested.
- $\overline{\underline{3/}}$ Repeat pin combination I for each named Power supply and for ground

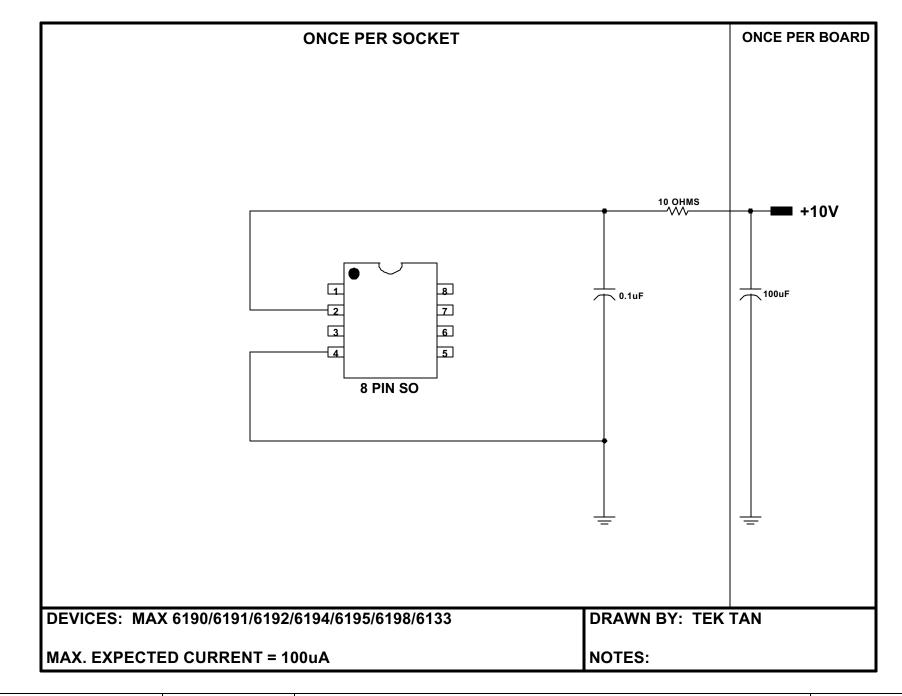
(e.g., where V_{PS1} is V_{DD} , V_{CC} , V_{SS} , V_{BB} , GND, $+V_{S}$, $-V_{S}$, V_{REF} , etc).

3.4 Pin combinations to be tested.

- a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
- b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., V_{SS1}, or V_{SS2} or V_{SS3} or V_{CC1}, or V_{CC2}) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
- c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.







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